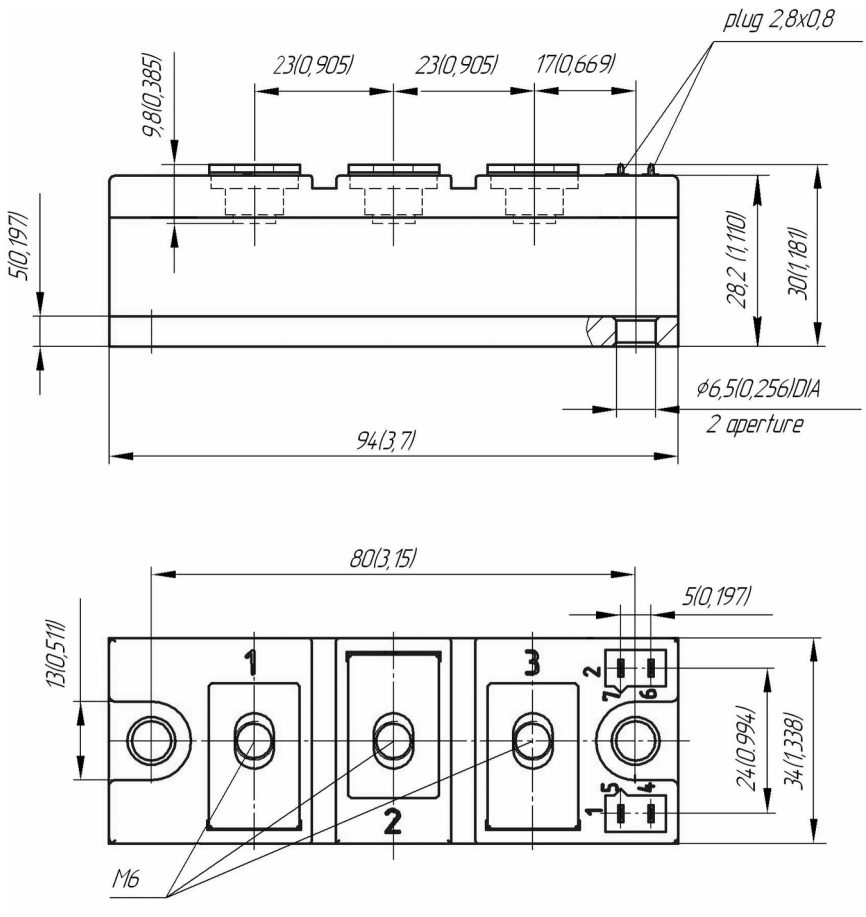
Diode Modules
MDx-155-36-F

Average forward current		I_{FAV}	155 A	
Repetitive peak reverse voltage		V_{RRM}	3000...3600 V	
V_{RRM}, V	3000	3200	3400	3600
Voltage code	30	32	34	36
T_j, °C	–40...+150			

MD3	MD4	MD5
		



MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{FAV}	Maximum allowable average forward current	A	179 155	T_c= 100 °C; T_c= 109 °C; 180° half-sine wave; 50 Hz	
I_{FRMS}	RMS forward current	A	243	T_c= 109 °C; 180° half-sine wave; 50 Hz	
I_{FSM}	Surge forward current	kA	4.5 5.0	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=10 ms; single pulse; V_R=0 V
			4.5 5.0	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=8.3 ms; single pulse; V_R=0 V
I^2t	Safety factor	$A^2s\cdot10^3$	100 120	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=10 ms; single pulse; V_R=0 V
			80 100	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=8.3 ms; single pulse; V_R=0 V
BLOCKING					
V_{RRM}	Repetitive peak reverse voltages	V	3000...3600	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; 50 Hz	
V_{RSM}	Non-repetitive peak reverse voltages	V	3100...3700	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; single pulse	
V_R	Reverse continuous voltages	V	$0.6\cdot V_{RRM}$	T_j=$T_{j\,max}$	
THERMAL					
T_{stg}	Storage temperature	°C	–40...+50		
T_j	Operating junction temperature	°C	–40...+150		
$T_{c\,op}$	Operating temperature	°C	–40...+125		
MECHANICAL					
a	Acceleration under vibration	m/s^2	50		

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{FM}	Peak forward voltage, max	V	1.70	T_j=25 °C; I_{FM}=500 A	
$V_{F(TO)}$	Forward threshold voltage, max	V	0.886	T_j=$T_{j\,max}$; 0.5 π I_{FAV} < I_T < 1.5 π I_{FAV}	
r_T	Forward slope resistance, max	mΩ	1.709		
BLOCKING					
I_{RRM}	Repetitive peak reverse current, max	mA	50 2.50	T_j=$T_{j\,max}$ T_j=25 °C	V_R=V_{RRM}
SWITCHING					
Q_r	Recovered charge, max	μC	2150	T_j=$T_{j\,max}$; I_{FM}=I_{FAV}; di_R/dt=-5 A/μs; V_R=100 V	
t_{rr}	Reverse recovery time, max	μs	65		
I_{rr}	Reverse recovery current, max	A	66		
THERMAL					
R_{thjc}	Thermal resistance, junction to case				
	per module	°C/W	0.0850	180° half-sine wave, 50 Hz	
	per arm	°C/W	0.1700		
	per module	°C/W	0.0800	DC	
	per arm	°C/W	0.1600		
R_{thch}	Thermal resistance, case to heatsink				
	per module	°C/W	0.0300		
	per arm	°C/W	0.0600		
INSULATION					
V_{ISOL}	Insulation test voltage	kV	3.00	Sine wave, 50 Hz; RMS	t=60 sec
			3.60		t=1 sec

MECHANICAL				
M_1	Mounting torque (M6)[1)]	Nm	6.00	Tolerance ± 15%
M_2	Terminal connection torque (M6)[1)]	Nm	6.00	Tolerance ± 15%
m	Weight, max	g	350	

PART NUMBERING GUIDE	NOTES
MD 3 - 155 - 36 - F - N 1 2 3 4 5 6 1. MD - Rectifier Diode 2. Circuit Schematic 3. Average Forward Current, A 4. Voltage Code 5. Package Type (M.F) 6. Ambient Conditions: N – Normal	[1)] The screws must be lubricated

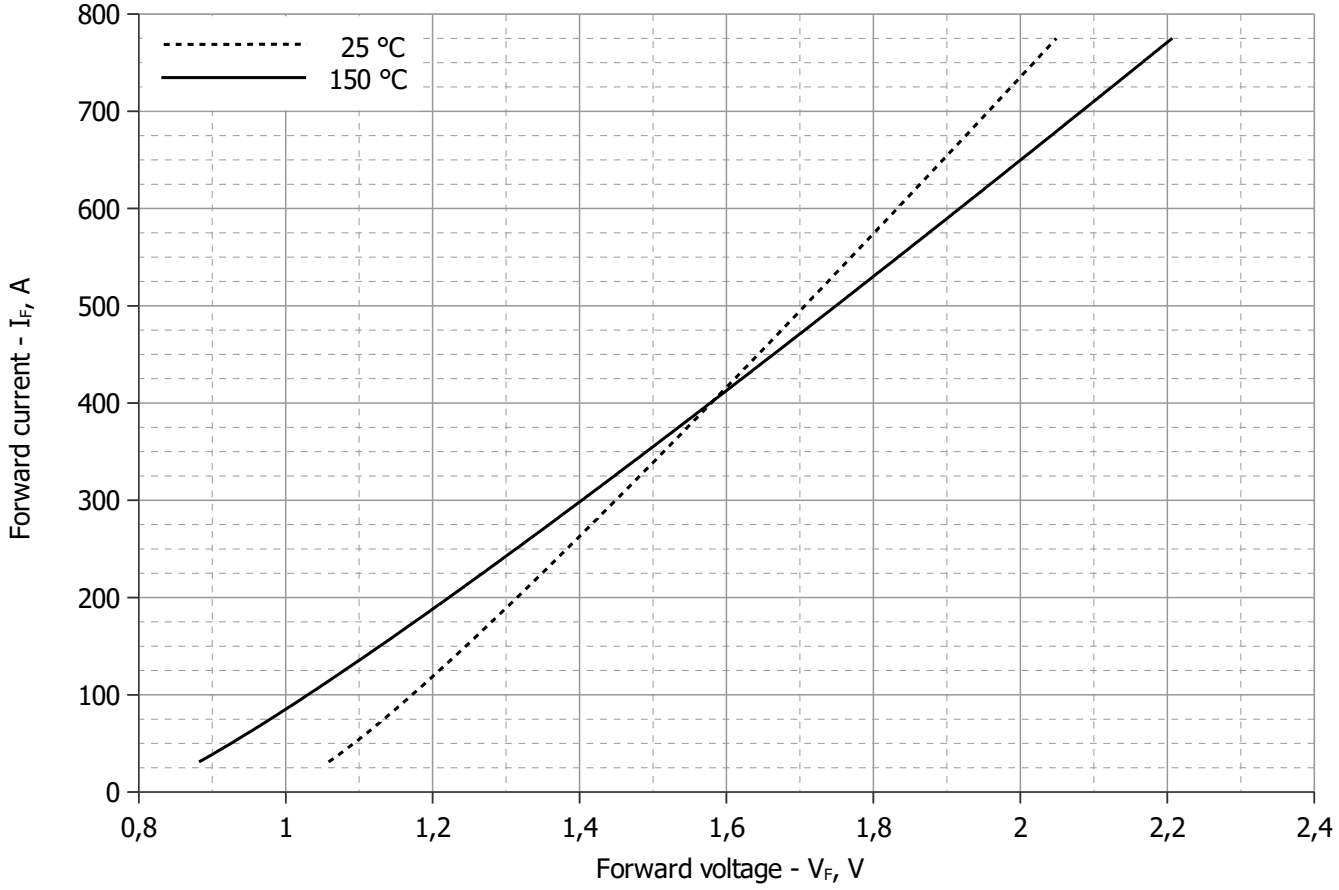


Fig 1 – Forward characteristics of Limit device

Analytical function for Forward characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	T_j = 25°C	$T_j = T_{j\,max}$
A	0.96353326	0.79443784
B	0.00109768	0.00139463
C	0.00648445	-0.01022551
D	0.00688546	0.01434426

Forward characteristic model (see Fig. 1).

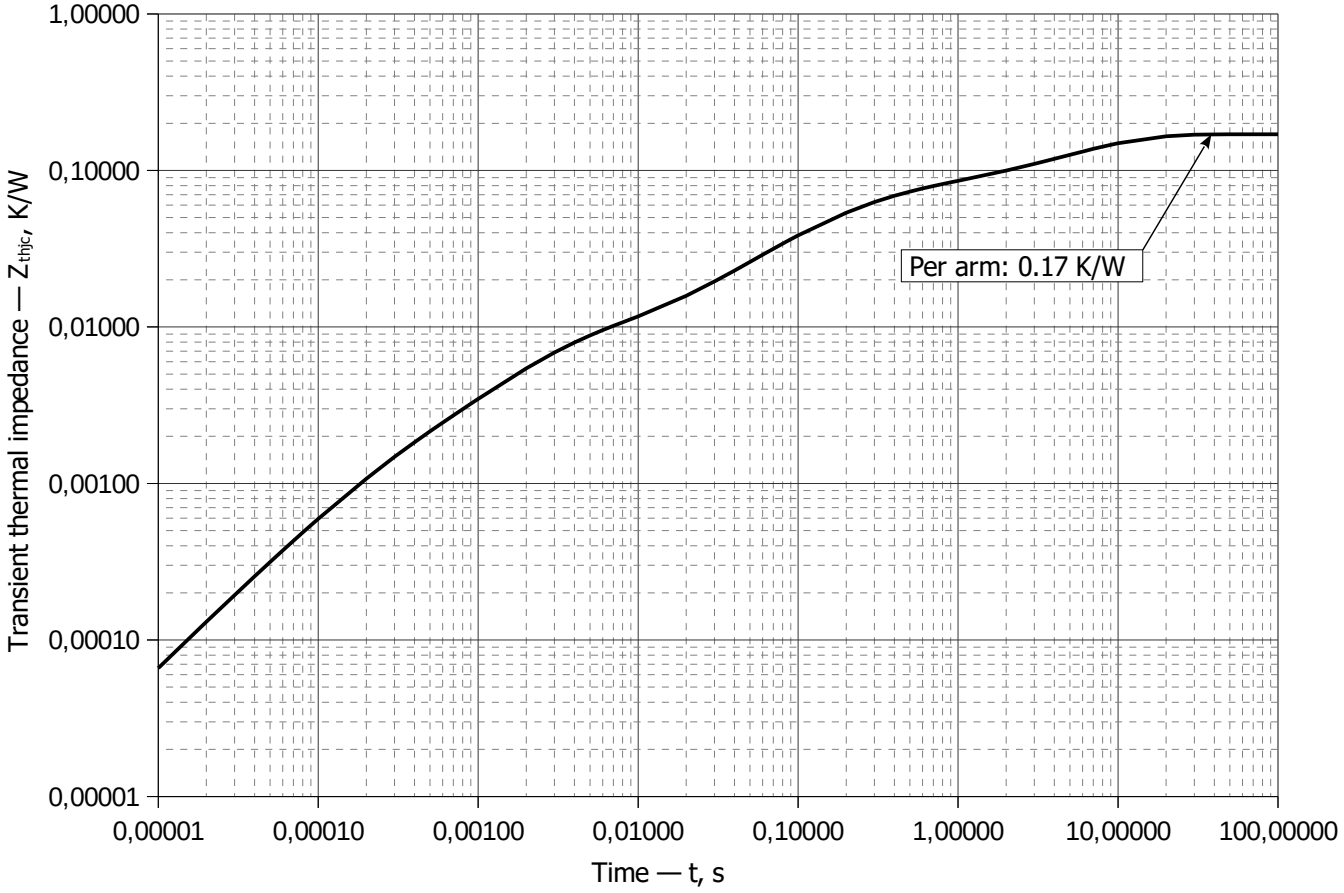


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^{n} R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where ***i*** = 1 to ***n***, ***n*** is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t.

R_i = Amplitude of p_{th} term.

τ_i = Time constatnt of r_{th} term.

i	1	2	3	4	5	6
R_i, K/W	0.0007228424	0.006639986	0.0153862565	0.0389709604	0.0142906115	0.09398934
τ_i, s	0.0002111	0.002366	0.06905	0.1909	0.6646	6.64

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

Fig 3 - Maximum recovered charge Q_{r-i} (integral) vs. commutation rate di_R/dt

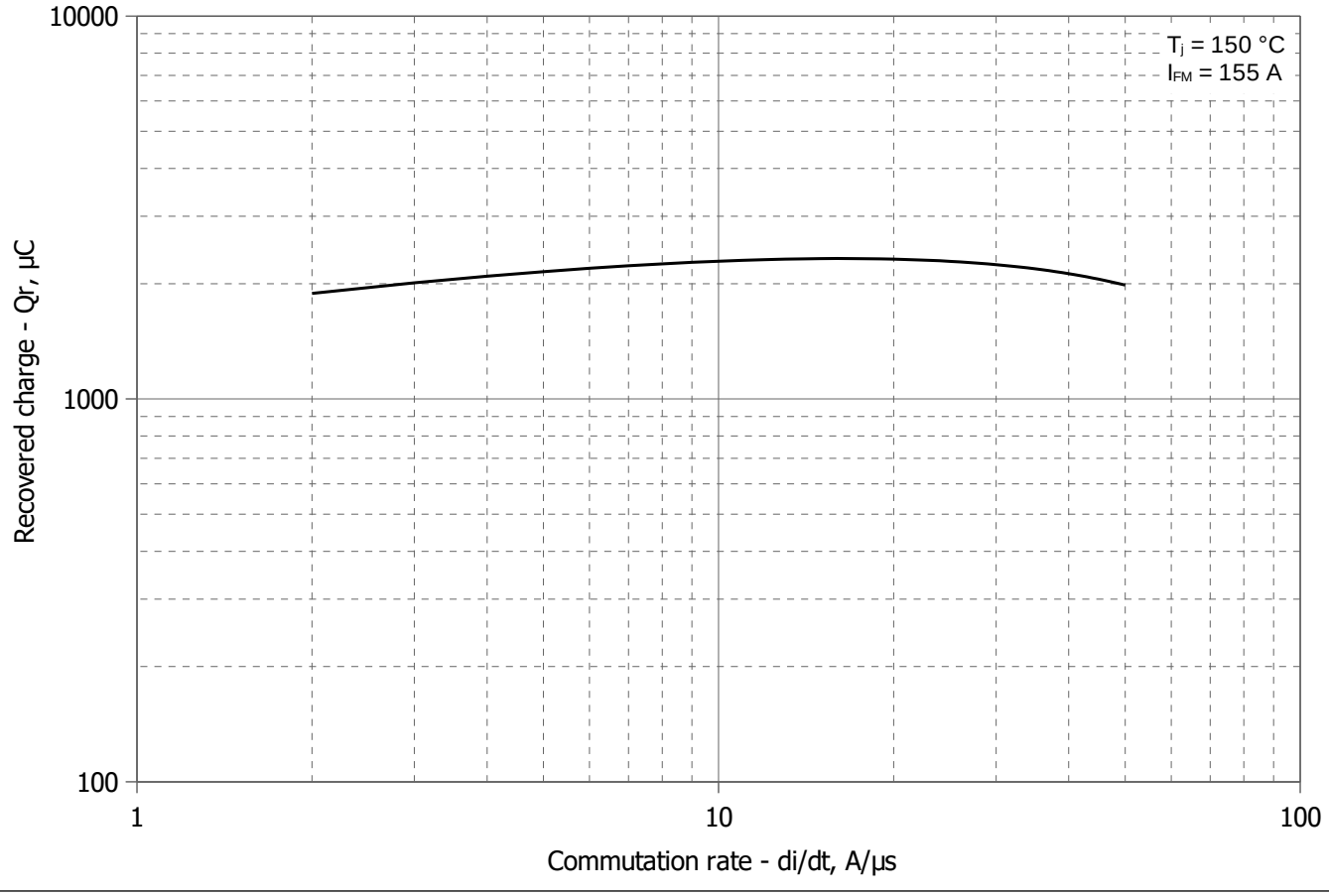


Fig 4 - Maximum recovered charge Q_r vs. commutation rate di_R/dt (25% chord)

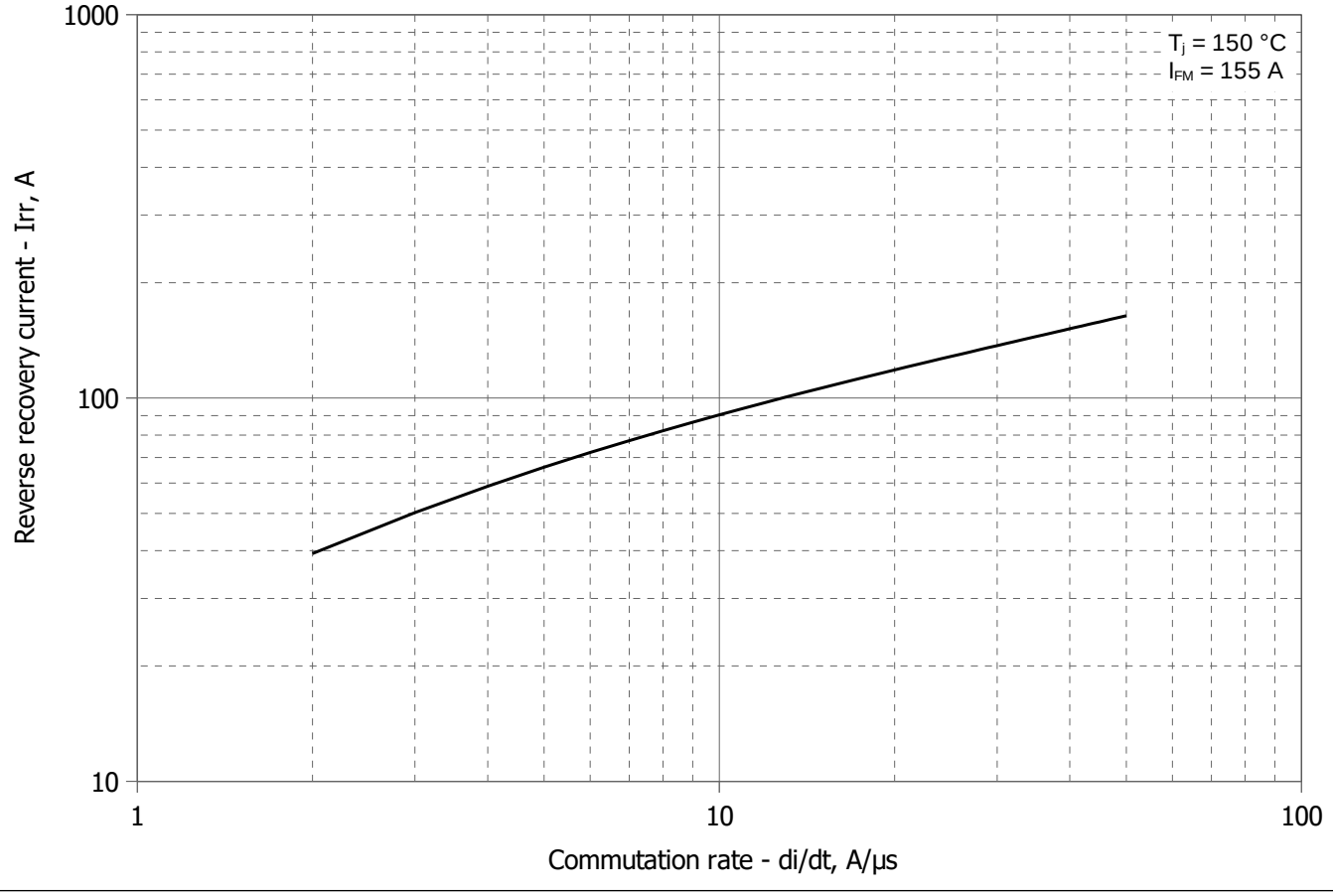


Fig 5 - Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

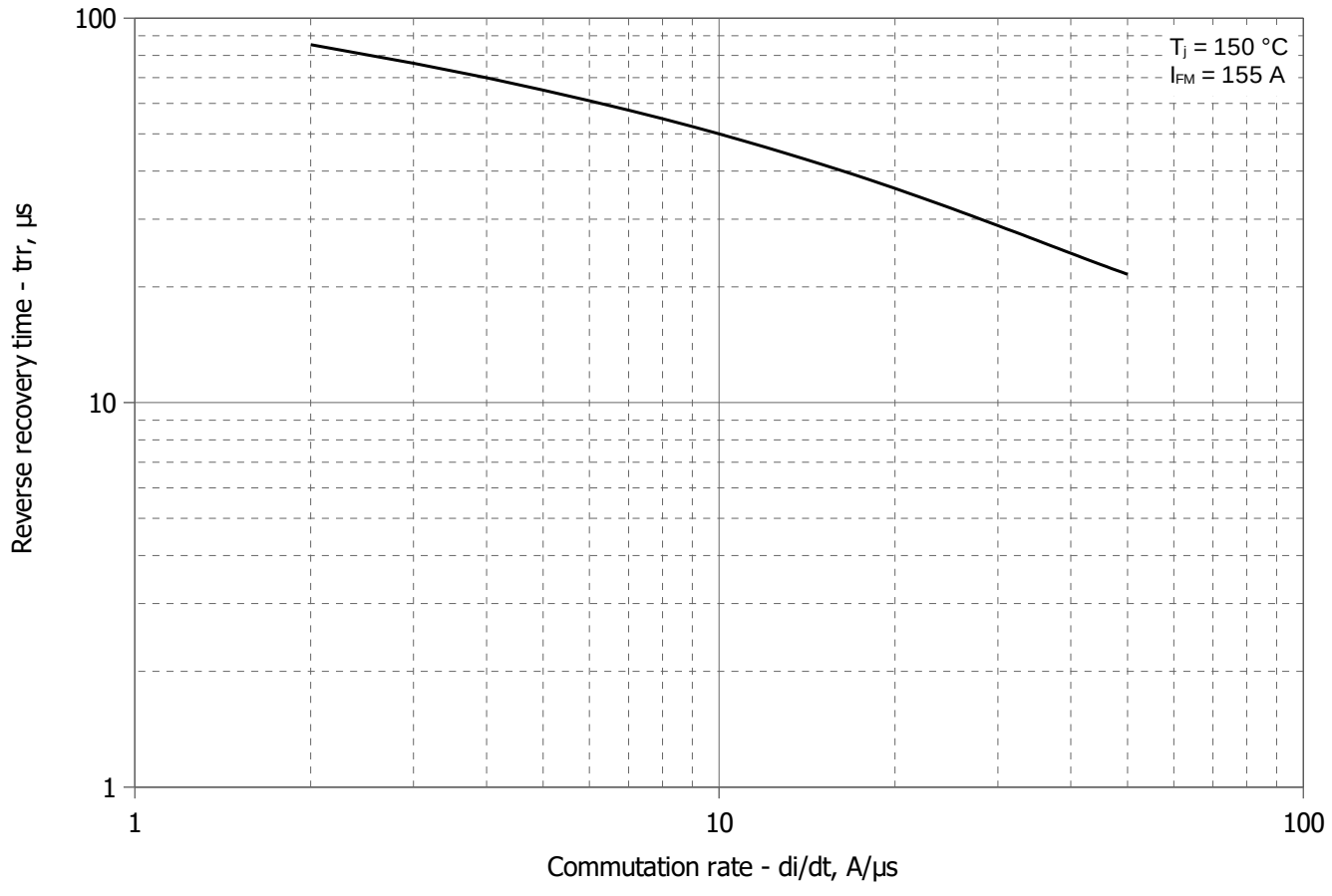


Fig 6 - Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

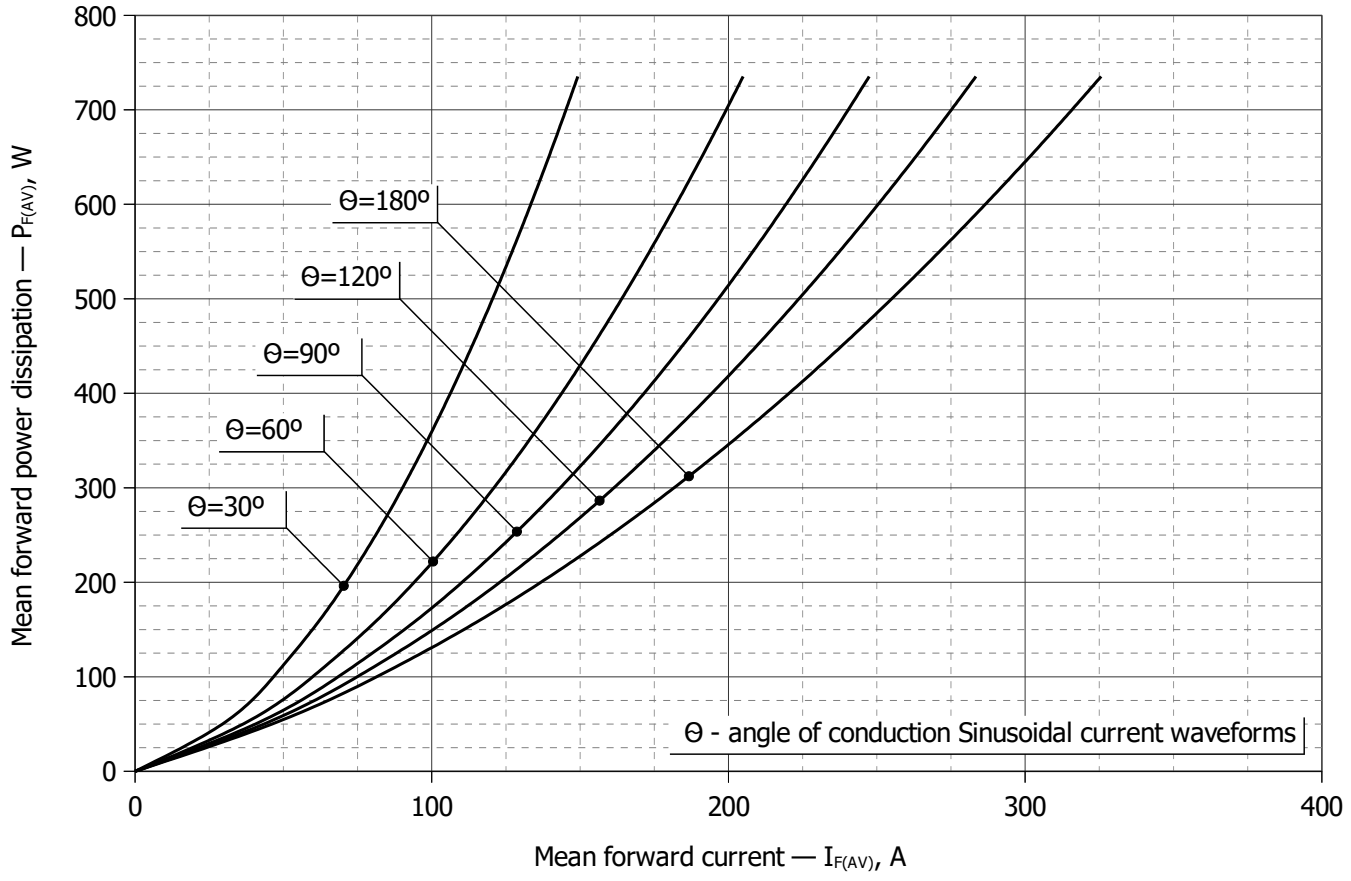


Fig. 7 - Mean forward power dissipation P_{FAV} vs. mean forward current I_{FAV} for sinusoidal current waveforms at different conduction angles (f=50Hz)

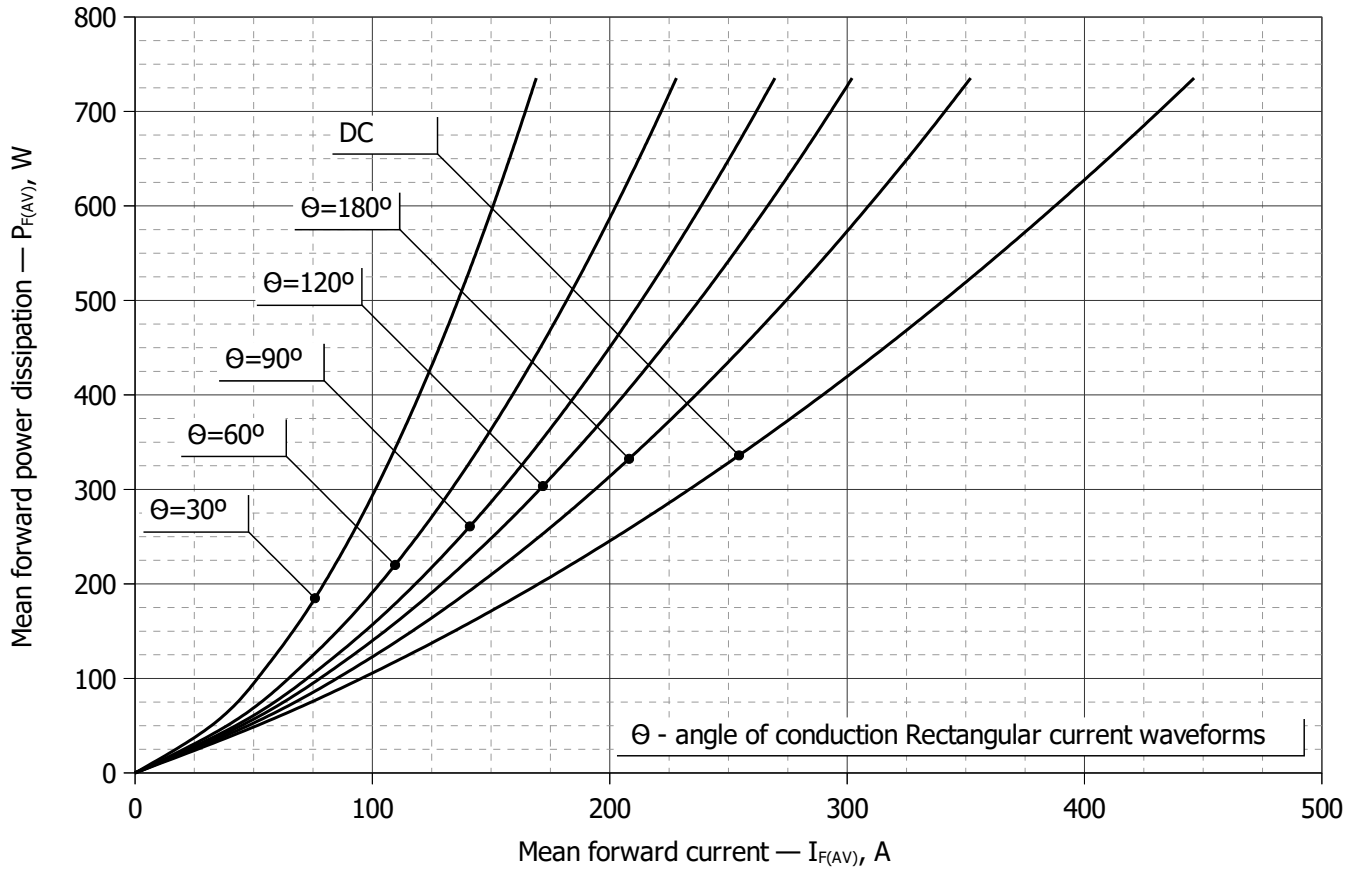


Fig. 8 – Mean forward power dissipation P_{FAV} vs. mean forward current I_{FAV} for rectangular current waveforms at different conduction angles and for DC (f=50Hz)

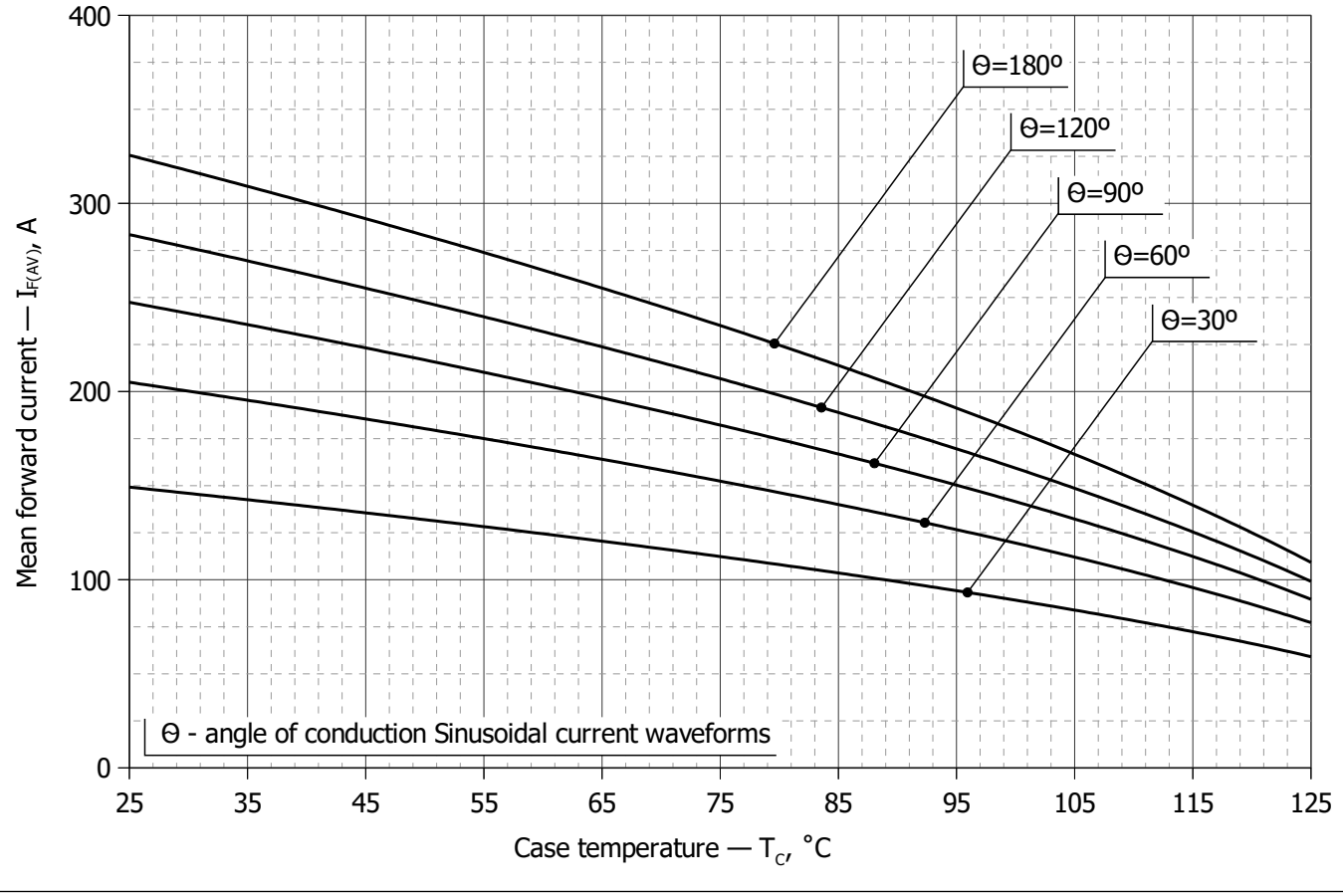


Fig. 9 – Mean forward current I_{FAV} vs. case temperature T_C for sinusoidal current waveforms at different conduction angles (f=50Hz)

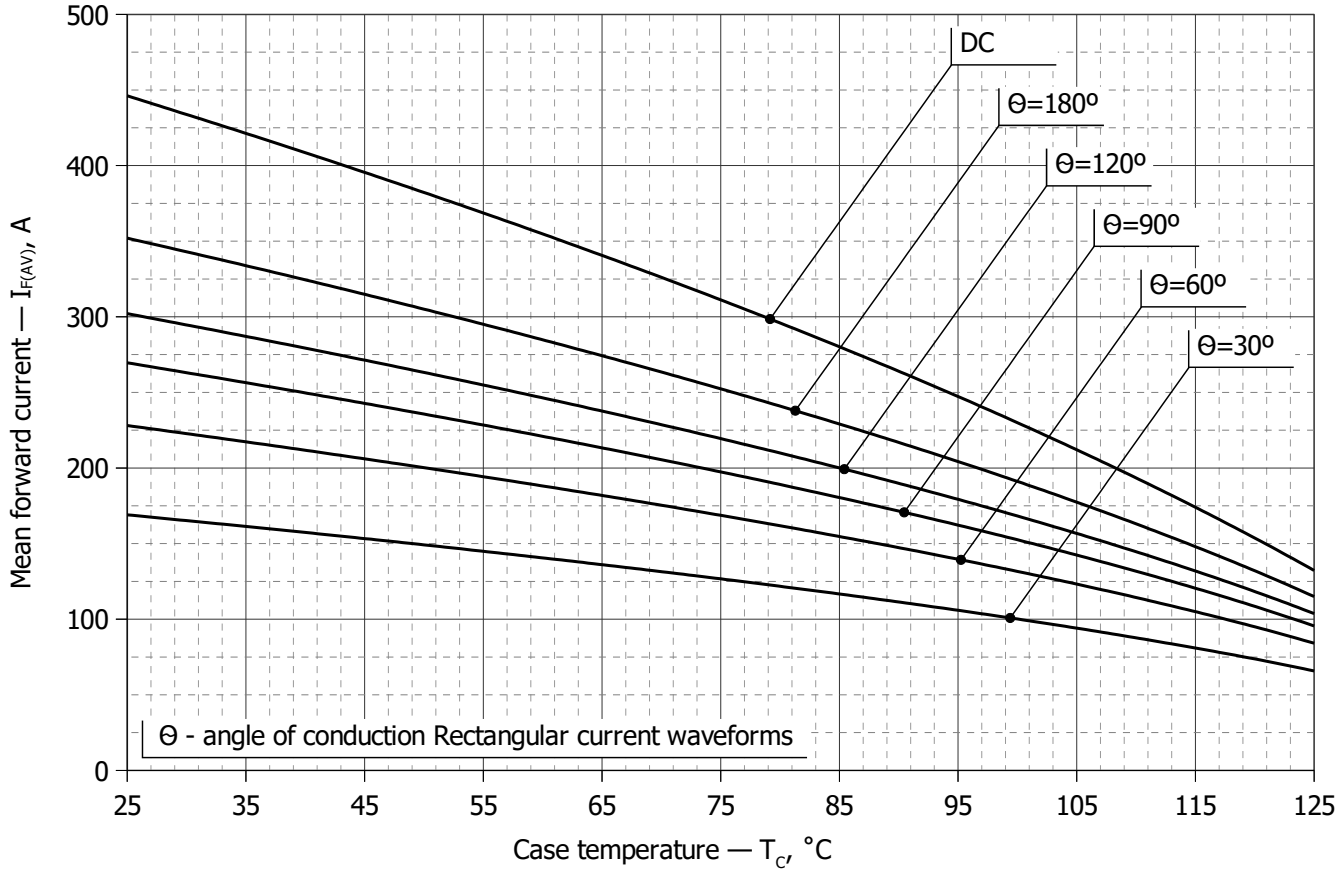


Fig. 10 - Mean forward current I_{FAV} vs. case temperature T_C for rectangular current waveforms at different conduction angles and for DC (f=50Hz)

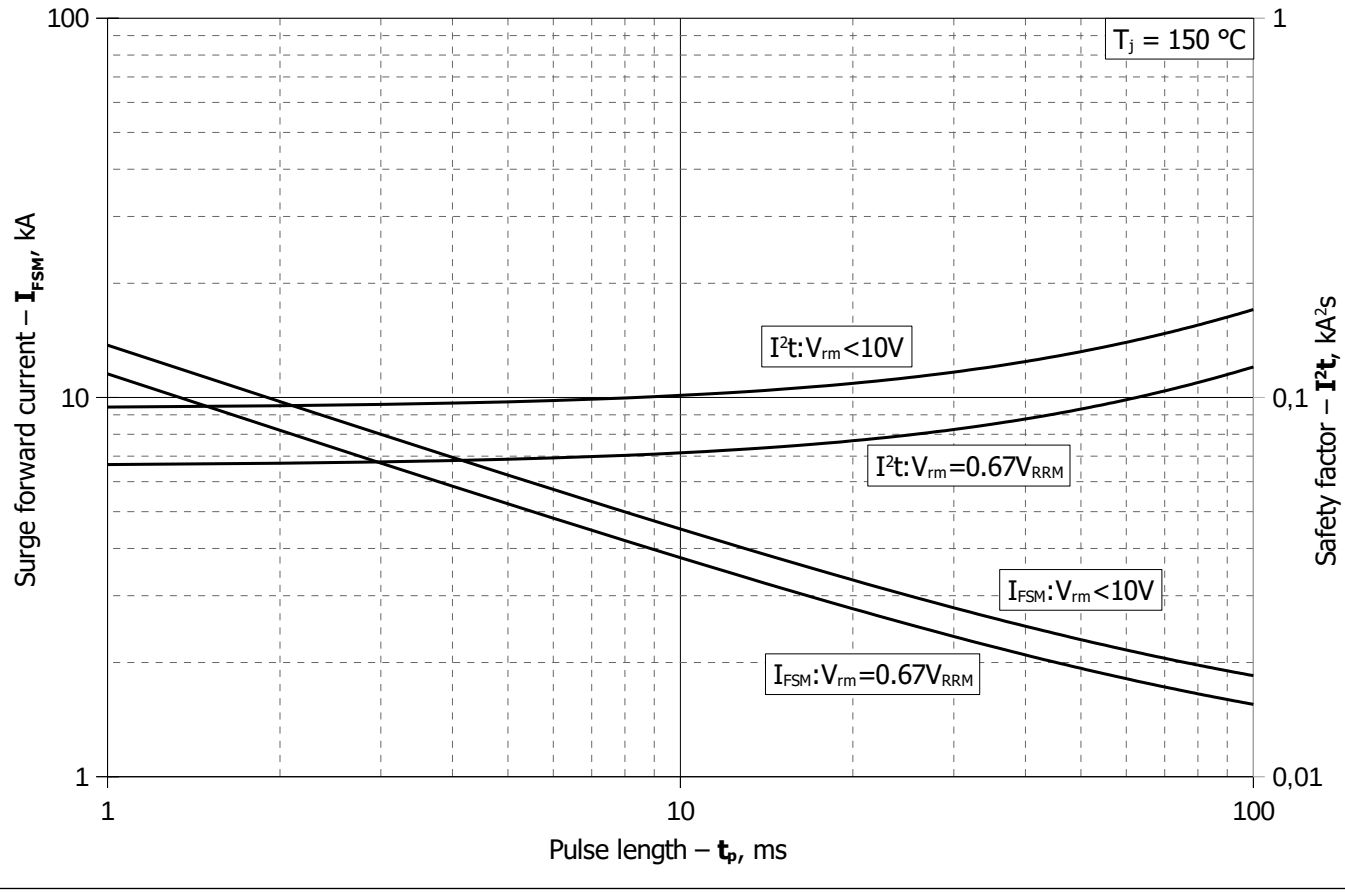


Fig. 11 – Maximum surge forward current I_{FSM} and safety factor I^2t vs. pulse length t_p

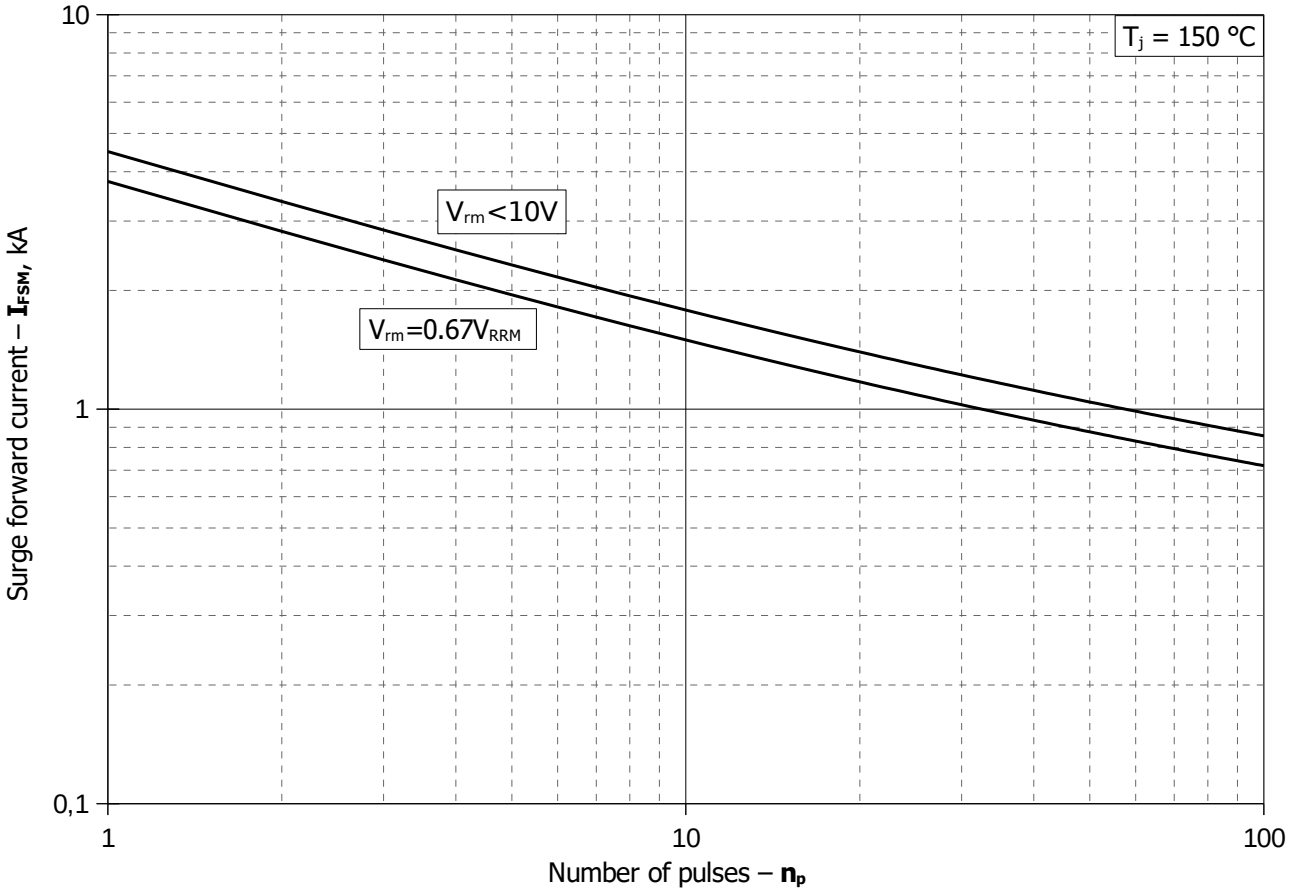


Fig. 12 – Maximum surge forward current I_{FSM} vs. number of pulses n_p